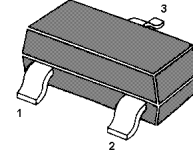
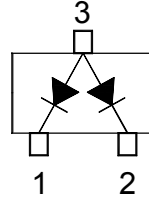


## SILICON EPITAXIAL PLANAR DIODE SCHOTTKY BARRIER DIODE

for high speed switching circuit and small current rectification applications



Marking Code: **FZ**  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	30	V
Reverse Voltage	$V_R$	30	V
Non-repetitive Peak Surge Current	$I_{FSM}$	1	A
Average Forward Current	$I_O$	200	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-55 to +125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	-	-	0.55	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	-	-	50	$\mu\text{A}$
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	$C_T$	-	30	-	pF
Reverse Recovery Time at $I_R = I_F = 10\text{ mA}$	$t_{rr}$	-	3	-	ns

